TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74VHC27F, TC74VHC27FN, TC74VHC27FT

### TRIPLE 3-INPUT NOR GATE

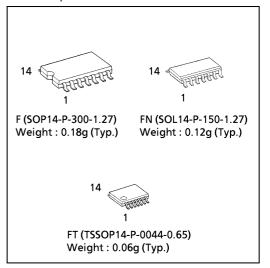
The TC74VHC27 is an advanced high speed CMOS 3-INPUT NOR GATE fabricated with silicon gate  $C^2MOS$  technology. It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is composed of 3 stages including buffer output, which provide high noise immunity and stable output. An input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3V systems and two supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

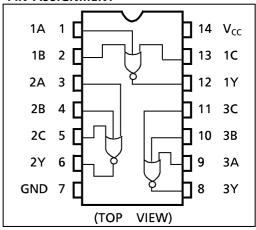
### **FEATURES:**

- High Speed------t<sub>pd</sub> = 4.1ns(typ.) at  $V_{CC} = 5V$
- Low Power Dissipation  $I_{CC} = 2\mu A(Max.)$  at  $Ta = 25^{\circ}C$
- High Noise Immunity  $V_{NIH} = V_{NIL} = 28\% V_{CC}$  (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays  $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range  $\cdots$   $V_{CC}$  (opr) =  $2V \sim 5.5V$
- Pin and Function Compatible with 74ALS27

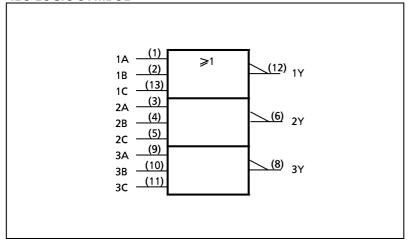
(Note) The JEDEC SOP (FN) is not available in Japan.



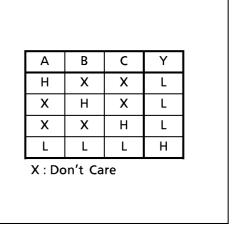
### **PIN ASSIGNMENT**



### **IEC LOGIC SYMBOL**



# TRUTH TABLE



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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

### **ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	-0.5~7.0	V
DC Input Voltage	V <sub>IN</sub>	-0.5~7.0	V
DC Output Voltage	V <sub>OUT</sub>	$-0.5 \sim V_{CC} + 0.5$	V
Input Diode Current	I <sub>IK</sub>	-20	mA
Output Diode Current	I <sub>OK</sub>	± 20	mA
DC Output Current	I <sub>OUT</sub>	± 25	mA
DC V <sub>CC</sub> /Ground Current	I <sub>CC</sub>	± 50	mA
Power Dissipation	P <sub>D</sub>	180	mW
Storage Temperature	T <sub>stg</sub>	<b>−65~150</b>	°C

### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	$V_{cc}$	2.0~5.5	V
Input Voltage	VIN	0~5.5	٧
Output Voltage	V <sub>OUT</sub>	0~V <sub>cc</sub>	V
Operating Temperature	T <sub>opr</sub>	<b>−40~85</b>	°C
Input Rise and Fall Time	dt/dv	$0\sim100 \ (V_{CC} = 3.3 \pm 0.3 V)$ $0\sim20 \ (V_{CC} = 5 \pm 0.5 V)$	ns / V

### DC ELECTRICAL CHARACTERISTICS

PARAMETER SYMBOL		TEST CONDITION		V <sub>cc</sub>	Т	Ta = 25°C			Ta = - 40~85°C	
		1 1231 CC	(V)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT	
High - Level					1.50	-	_	1.50	_	
Input Voltage	V <sub>IH</sub>		3.0~ 5.5	$V_{cc} \times 0.7$	_	_	$V_{cc} \times 0.7$	_	V	
Low - Level Input Voltage				2.0		-	0.50	-	0.50	V
			3.0~ 5.5	_	_	$V_{cc} \times 0.3$	_	$V_{cc} \times 0.3$		
High - Level Output Voltage		$V_{IN} = V_{IL}$	$I_{OH} = -50\mu A$	2.0	1.9	2.0	_	1.9	_	v
	V <sub>OH</sub>			3.0 4.5	2.9 4.4	3.0 4.5	_	2.9 4.4	_	
			$I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94	_	_	2.48 3.80	-	
Low - Level Output Voltage		$V_{OL} V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 50 \mu A$	2.0	_	0.0	0.1	_	0.1	
	V <sub>OL</sub>			3.0 4.5	_	0.0 0.0	0.1 0.1	_	0.1 0.1	٧
			I <sub>OL</sub> = 4mA I <sub>OL</sub> = 8mA	3.0 4.5	_	_	0.36 0.36	_	0.44 0.44	
Input Leakage Current	I <sub>I N</sub>	$V_{IN} = 5.5V$ or GND		0~5.5	_	_	±0.1	_	± 1.0	^
Quiescent Supply Current	I <sub>cc</sub>	$V_{IN} = V_{CC}$ or GN	5.5		_	2.0	_	20.0	$\mu$ <b>A</b>	

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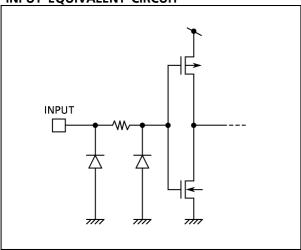
PARAMETER	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -4	UNIT		
			V <sub>CC</sub> (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
Propagation Delay Time	t <sub>pLH</sub> t <sub>pHL</sub>		3.3 ± 0.3	15	_	6.2	8.8	1.0	10.5	nc
			3.3 ± 0.3	50	_	8.7	12.3	1.0	14.0	
		5.0 ± 0.5	15		4.1	5.9	1.0	7.0	ns	
			3.0 ± 0.5	50		5.6	7.9	1.0	9.0	
Input Capacitance	C <sub>I N</sub>		·		_	4	10	_	10	nE
Power Dissipation Capacitance	C <sub>PD</sub>	(	Note 1)		_	20	_	_	_	pF

Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

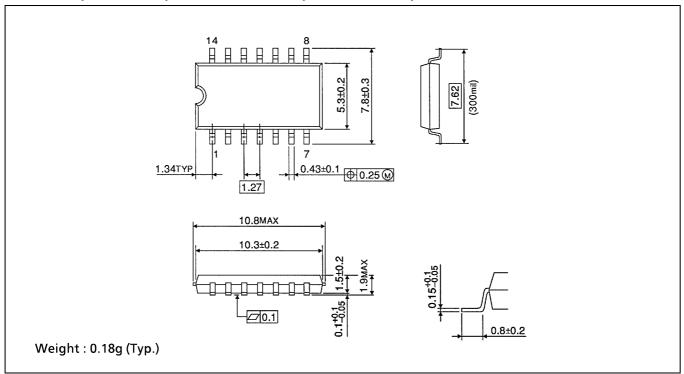
$$I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 3 \text{ (per Gate)}$$

# INPUT EQUIVALENT CIRCUIT



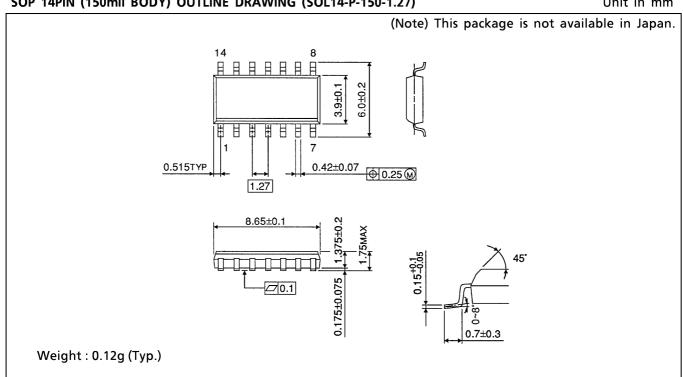
# SOP 14PIN (200mil BODY) OUTLINE DRAWING (SOP14-P-300-1.27)

Unit in mm



# SOP 14PIN (150mil BODY) OUTLINE DRAWING (SOL14-P-150-1.27)

Unit in mm



# TSSOP 14PIN OUTLINE DRAWING (TSSOP14-P-0044-0.65) Unit in mm 0.55TYP 0.5